

ANTIFERROMAGNETICALLY STABILIZED PSEUDO SPIN VALVE FOR MEMORY APPLICATIONS

Abstract of the Disclosure

The invention relates to improving the switching reliability of a magnetic memory cell in a magnetic random access memory (MRAM). Embodiments of the invention add an antiferromagnet to a magnetic memory cell. An antiferromagnetic layer can be formed adjacent to a soft layer in the MRAM on a side of the soft layer that is opposite to a hard layer of the MRAM. One embodiment further includes an additional interlayer of non-antiferromagnetic material between the antiferromagnetic layer and the soft layer.

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